Correction: High density and patternable growth of silicon, germanium and alloyed SiGe nanowires by a rapid anneal protocol

M. Bezuidenhout, T. Kennedy, S. Belochapkin, Y. Guo, E. Mullane, P. A. Kiely and K. M. Ryan*

Correction for 'High density and patternable growth of silicon, germanium and alloyed SiGe nanowires by a rapid anneal protocol' by M. Bezuidenhout et al., J. Mater. Chem. C, 2015, 3, 7455–7462.

Ref. 49 of the manuscript has been updated as follows:


The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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